Shanghai Fudan Microelectronics Group Company Limited



FM24C64D 2-Wire Serial EEPROM

With Unique ID and Security Sector

Data Sheet

Jun. 2015



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Description

The FM24C64D provides 65,536 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 8,192 words of 8 bits each, with 128-bit UID and 32-byte Security Sector. The device's cascadable feature allows up to 8 devices to share a common 2-wire bus. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operations are essential.

Features

- Low Operation Voltage: V_{cc} = 1.7V to 5.5V
- Internally Organized: 8,192 x 8
- 2-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bi-directional Data Transfer Protocol
- 1MHz (2.5V~5.5V) and 400 kHz (1.7V) Compatibility
- Write Protect Pin for Hardware Data Protection
- 32-Byte Page Write Modes (Partial Page Writes are Allowed)
- Lockable 32-Byte Security Sector
- 128-Bit Unique ID for each device
- Self-timed Write Cycle (5 ms max)
- High-reliability
 - Endurance: 1,000,000 Write Cycles
 - Data Retention: 40 Years
- PDIP8 Package (RoHS Compliant)
- SOP8, TSSOP8, TDFN8 and Thin 4-ball WLCSP Packages (RoHS Compliant and Halogen-free)

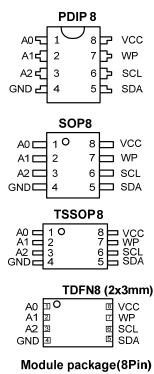
Absolute Maximum Ratings

Operating Temperature (Plastic Package)	-55°C to +125°C
Operating Temperature (Module Package)	-20°C to +60°C
Storage Temperature (Plastic Package)	-65°C to +150°C
Storage Temperature (Module Package)	-25°C to +70°C
Voltage on Any Pin with Respect to Ground	-1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

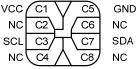
*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Packaging Type



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Thin 4-ball WLCSP¹



Note:

Please contact local sales office for detail description.

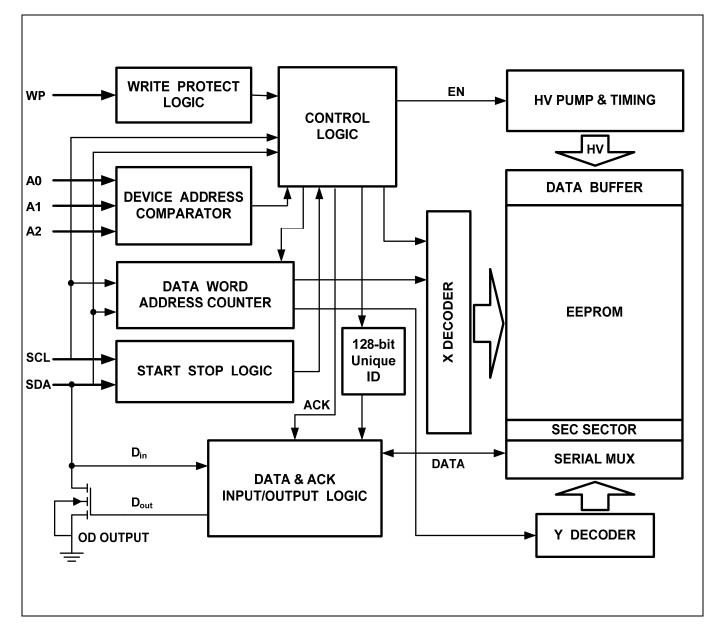
Pin Configurations

Pin Name	Function
A0~A2	Device Address Inputs
SDA	Serial Data Input/Output
SCL	Serial Clock Input
WP	Write Protect
V _{CC}	Power Supply
GND	Ground
NC	Not Connect

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Figure 1. Block Diagram



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Pin Description

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

DEVICE ADDRESSES (A2, A1, A0): The A2, A1 and A0 pins are device address inputs that are hardwired or left not connected for hardware compatibility with other FM24CXX devices. When the pins are hardwired, as many as eight 64K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section). If the pins are left floating, the A2, A1 and A0 pins will be internally

pulled down to GND if the capacitive coupling to the circuit board V_{CC} plane is <3pF, if coupling is >3pF, FMSH recommends connecting the address pins to GND.

WRITE PROTECT (WP): The FM24C64D has a Write Protect pin that provides hardware data protection. The WP pin allows normal write operations when connected to ground (GND). When the Write Protect pin is connected to VCC, all write operations to the memory are inhibited. If the pin is left floating, the WP pin will be internally pulled down to GND if the capacitive coupling to the circuit board Vcc plane is <3pF. If coupling is >3pF, FMSH recommends connecting the WP to GND. Switching WP to VCC prior to a write operation creates a software write protected function.

Write Protect Description

WD Din Status	Part of the Memory Protected
WP Pin Status	FM24C64D
WP=V _{CC}	Full Memory
WP=GND	Normal Read/Write Operations

Memory Organization

FM24C64D, 64K SERIAL EEPROM: Internally organized with 256 pages of 32 bytes each, the 64K requires a 13-bit data word address for random word addressing.

Security Sector : The FM24C64D offers 32-byte Security Sectors which can be written and (later) permanently locked in Read-only mode. This memory may be used by the system manufacturers to store security and other important information separately from the main memory array.

Device ADDR	Page ADDR	Byte Number						
Device ADDR	Fage ADDR	31	31					
1010	0 1 2 255		Data Memory (256P X 32B)					
1011	xxxx x00x xxxx xxxx ¹	Security Sector (32 Bytes)						
1011	xxxx xx1x xxxx xxxx ²	Unique ID(128 Bits)						

Note: 1. Address bits ADDR<10:9> must be 00, ADDR<4:0> define byte address, other bits are don't care 2. Address bits ADDR<10:9> must be x1, ADDR<3:0> define byte address, other bits are don't care



Pin Capacitance

SYMBOL	PARAMETER	CONDITIONS	Max	Units
C _{IN} ¹	Input Capacitance	$V_{IN} = 0V, f = 1MHz$	6	рF
C _{OUT} ¹	Output Capacitance	$V_{OUT} = 0V, f = 1MHz$	8	рF

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.7V$ to +5.5V, (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V _{CC}	Supply Voltage		1.7		5.5	V
I _{CC1}	Supply Current	V_{CC} = 5.0V, Read at 400KHz		0.4	1.0	mA
I _{CC2}	Supply Current	V_{CC} = 5.0V, Write at 400KHz		2.0	3.0	mA
I _{SB1}	Standby Current	V_{CC} = 1.7V, V_{IN} = V_{CC}/V_{SS}			1.0	μA
I _{SB2}	Standby Current	V_{CC} = 5.5V, V_{IN} = V_{CC}/V_{SS}			6.0	μA
ILI	Input Leakage Current	$V_{IN} = V_{CC}/V_{SS}$		0.1	3.0	μA
I _{LO}	Output Leakage Current	$V_{OUT} = V_{CC} / V_{SS}$		0.05	3.0	μA
V_{IL}^{1}	Input Low Level		-0.6		V _{CC} x 0.3	V
V _{IH} ¹	Input High Level		$V_{CC} x 0.7$		V _{CC} + 0.5	V
V _{OL2}	Output Low Level 2	V_{CC} = 3.0V, I_{OL} = 2.1 mA			0.4	V
V _{OL1}	Output Low Level 1	V_{CC} =1.7V, I_{OL} = 0.15 mA			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

AC Characteristics

400 kHz AC characteristics

Recommended operating conditions: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.7V$ to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
f _{SCL}	Clock Frequency, SCL		400	kHz
t _{LOW}	Clock Pulse Width Low	1.3		μs
t _{HIGH}	Clock Pulse Width High	0.6		μs
t _i 1	Noise Suppression Time		80	ns
t _{AA}	Clock Low to Data Out Valid	0.1	0.9	μs
t _{BUF} ¹	Time the bus must be free before a new transmission can Start	1.3		μs
t _{HD.STA}	Start Hold Time	0.6		μs
t _{su.sta}	Start Setup Time	0.6		μs
t _{HD.DAT}	Data In Hold Time	0		μs
t _{SU.DAT}	Data In Setup Time	100		ns
t _R	Inputs Rise Time ¹		300	ns
t⊨	Inputs Fall Time ¹		300	ns
t _{su.sto}	Stop Setup Time	0.6		μs
t _{DH}	Data Out Hold Time	100		ns
t _{WR}	Write Cycle Time		5	ms
Endurance ¹	3.3V, 25°C, Page Mode 1,000,000		Write Cycles	

1 MHz AC characteristics

Recommended operating conditions: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +2.5V$ to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
f _{SCL}	Clock Frequency, SCL		1	MHz
t _{LOW}	Clock Pulse Width Low	500		ns
t _{HIGH}	Clock Pulse Width High	320		ns
t _l 1	Noise Suppression Time		80	ns
t _{AA}	Clock Low to Data Out Valid		450	ns
t _{BUF} ¹	Time the bus must be free before a new transmission can Start	500		ns
t _{HD.STA}	Start Hold Time	250		ns
t _{su.sta}	Start Setup Time	250		ns
t _{HD.DAT}	Data In Hold Time	0		ns
t _{SU.DAT}	Data In Setup Time	50		ns
t _R	Inputs Rise Time ¹		120	ns
t _F	Inputs Fall Time ¹		120	ns
t _{su.sto}	Stop Setup Time	250		ns
t _{DH}	Data Out Hold Time	100		ns
t _{WR}	Write Cycle Time		5	ms
ndurance ¹ 3.3V, 25°C, Page Mode 1,000,000		Write Cycles		

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- Notes: 1. This parameter is characterized and is not 100% tested.
 - 2. AC measurement conditions:

RL (connects to V_{CC}): 1.3 kΩInput pulse voltages: $0.3 V_{CC}$ to $0.7 V_{CC}$ Input rise and fall times: ≤ 50 ns Input and output timing reference voltages: $0.5 V_{CC}$

Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Figure 4). Data changes during SCL high periods will indicate a start or stop condition as defined below.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Figure 5).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Figure 5).

ACKNOWLEDGE: All address and data words are serially transmitted to and from the EEPROM in 8-bit

words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

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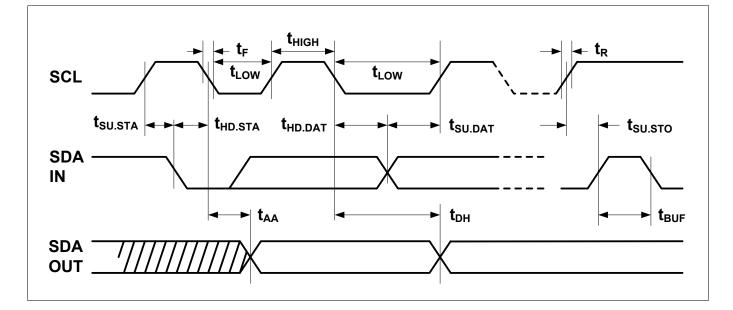
STANDBY MODE: The FM24C64D features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the stop bit and the completion of any internal operations.

Memory RESET: After an interruption in protocol, power loss or system reset, any 2-wire part can be reset in following these steps:

- 1. Clock up to 9 Cycles,
- 2. Look for SDA high in each cycle while SCL is high and then,
- 3. Create a start condition as SDA is high.

Bus Timing

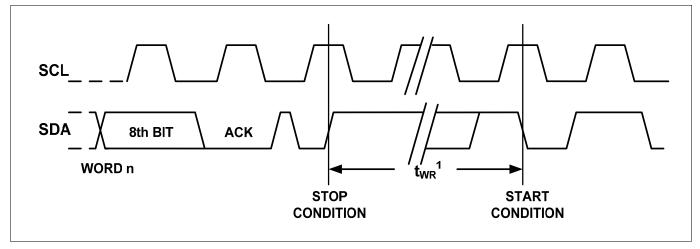






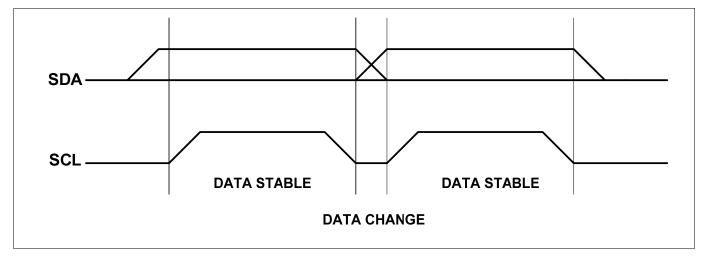
Write Cycle Timing



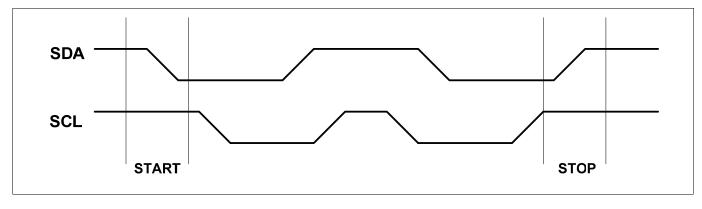


Note: 1. The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

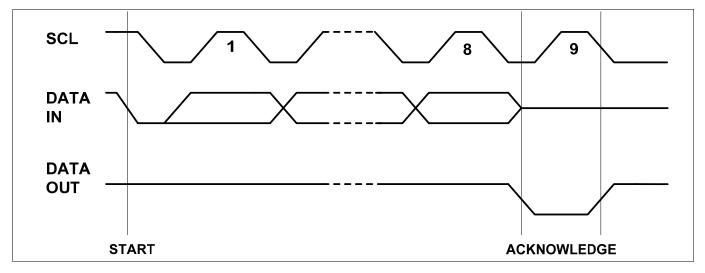
Figure 4. Data Validity











Device Addressing

DATA MEMORY ACCESS: The 64K EEPROM device requires a 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Table 1).

The device address word consists of a mandatory '1010'(Ah) sequence for the first four most significant bits as shown in Table 1. This is common to all the EEPROM devices.

The 64K EEPROM uses the three device address bits A2, A1, A0 to allow as many as eight devices on the same bus. These bits must compare to their corresponding hard-wired input pins. The A2, A1 and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The Module package device address word also consists of a mandatory '1010'(Ah) sequence for the first four most significant bits. The next 3 bits are all zero.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to a standby state.

UNIQUE ID ACCESS: The FM24C64D utilizes a separate memory block containing a factory programmed 128-bit unique ID. Access to this memory location is obtained by beginning the device

address word with a '1011'(Bh) sequence (refer to Table 1). The behavior of the next three bits (A2, A1 and A0) remains the same as during a standard memory addressing sequence.

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The eighth bit of the device address needs be set to a one to read the Serial Number. Writing or altering the 128-bit unique ID is not possible.

For more details on accessing this special feature, See Read Operations on page 14.

SECURITY SECTOR ACCESS: The FM24C64D offers 32-byte Security Sector which can be written and (later) permanently locked in Read-only mode. Access to this memory location is obtained by beginning the device address word with a '1011'(Bh) sequence (refer to Table 1). The behavior of the next three bits (A2, A1 and A0) remains the same as during a standard memory addressing sequence.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

For more details on accessing this special feature, See Write Operations and Read Operations on page 13,14.

NOISE PROTECTION: Special internal circuitry placed on the SDA and SCL pins prevent small noise spikes from activating the device.

DATA SECURITY: The Device has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at V_{CC} .



Table 1-1. Device Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	1	0	1	0	A2	A1	A0	R/W
Security Sector	1	0	1	1	A2	A1	A0	R/W
Security Sector Lock Bit	1	0	1	1	A2	A1	A0	R/W
Unique ID Number	1	0	1	1	A2	A1	A0	1
	MSB							LSB

Table 1-2. First Word Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	х	х	х	A12	A11	A10	A9	A8
Security Sector	х	х	х	х	х	0	0	х
Security Sector Lock Bit	х	х	х	х	х	1	0	Х
Unique ID Number	х	х	х	х	х	х	1	х
	MSB							LSB

NOTE: x = Don`t care bit.

Table 1-3. Second Word Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	A7	A6	A5	A4	A3	A2	A1	A0
Security Sector	х	х	х	A4	A3	A2	A1	A0
Security Sector Lock Bit	х	х	х	х	х	х	х	х
Unique ID Number	х	х	х	х	0	0	0	0
	MSB	•	•	•				LSB

NOTE: x = Don`t care bit.

Write Operations

BYTE WRITE: A write operation requires two 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle, t_{WR} to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see **Figure 7** on page 15).

PAGE WRITE: The 64K EEPROM is capable of 32-byte page writes. A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 31 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see **Figure 8** on page 15).

The data word address lower seven bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 32 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten. **ACKNOWLEDGE POLLING:** Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

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WRITE SECURITY SECTOR: Write the Security Sector is similar to the page write but requires use of device address, and the special word address seen in Table 1 on page 12. The higher address bits ADDR<12:5> are don't care except for address bits ADDR<10:9>, which must be equal to '00b'. Lower address bits ADDR<4:0> define the byte address inside the Security Sector (see **Figure 12** on page 16).

If the Security Sector is locked, the data bytes transferred during the Write Security Sector operation are not acknowledged (NoAck).

LOCK SECURITY SECTOR: Lock the Security Sector is similar to the byte write but requires use of device address, and special word address seen in Table 1 on page 12. The word address bits ADDR<10:9> must be '10b', all other word address bits are don't care. The data byte must be equal to the binary value 1111 1111(see **Figure 14** on page 17).

If the Security Sector is locked, the data bytes transferred during the Lock Security Sector operation are not acknowledged (NoAck).

Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (see **Figure 9** on page 15).

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (see Figure 10 on page 16).

SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (see **Figure 11** on page 16)

UNIQUE ID READ: Reading the serial number is similar to the sequential read but requires use of the device address, a dummy write, and the use of specific word address seen in Table 1 on page 12. The higher address bits ADDR<12:4> are don't care except for address bits ADDR<10:9>, which must be equal to 'x1b'. Lower address bits ADDR<3:0> define the byte address inside the UID. If the application desires to

read the first byte of the UID, the lower address bits ADDR<3:0> would need to be '0000b'.

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When the end of the 128-bit UID number is reached (16 bytes of data), the data word address will roll-over back to the beginning of the 128-bit UID number. The Unique ID Read operation is terminated when the microcontroller does not respond with a zero (ACK) and instead issues a Stop condition (see **Figure 16** on page 18).

READ SECURITY SECTOR : Read the Security Sector is similar to the random read but requires use of device address, a dummy write, and the use of specific word address seen in Table 1 on page 12. The higher address bits ADDR<12:5> are don't care except for address bits ADDR<10:9>, which must be equal to '00b'. The lower address bits ADDR<4:0> define the byte address inside the Security Sector.

The internal byte address is automatically incremented to the next byte address after each byte of data is clocked out. When the last byte (1Fh) is reached, it will roll over to 00h, the first byte of the Security Sector, and continue to increment. (see **Figure 13** on page 17).

READ LOCK STATUS: There are two ways to check the lock status of the Security Sector.

1. The first way is initiated by a Security Sector Write, the EEPROM will acknowledge if the Security Sector is unlocked, while it will not acknowledge if the Security Sector is locked.

Once the acknowledge bit is read, it is recommended to generate a Start condition followed by a Stop condition, so that:

- Start: the truncated command is not executed because the Start condition resets the device internal logic
- Stop: the device is then set back into Standby mode by the Stop condition.

2. The second way is initiated by a Lock Status Read. Lock Status Read is similar to the random read but requires use of device address seen in Table 1 on page 12, a dummy write, and the use of specific word address. The address bits ADDR<10:9> must be '10b', all other address bits are Don't Care. The Lock bit is the BIT1 of the byte read on SDA. It is at "1" when the lock is active and at "0" when the lock is not active. The same data is shifted out repeatedly until the microcontroller does not respond with a zero but does generate a following stop condition (see **Figure 15** on page 18).

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Figure 7. Byte Write

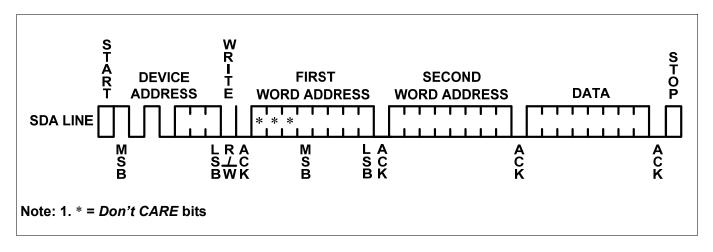


Figure 8. Page Write

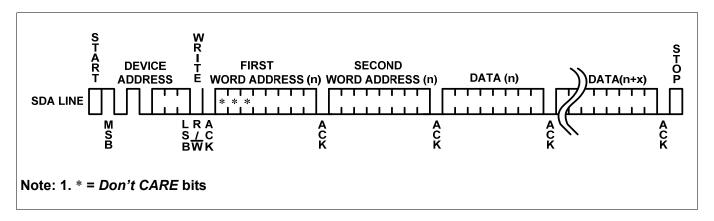


Figure 9. Current Address Read

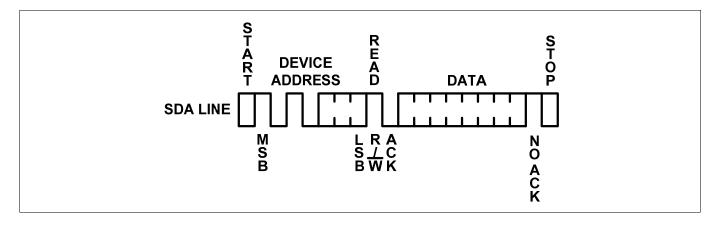
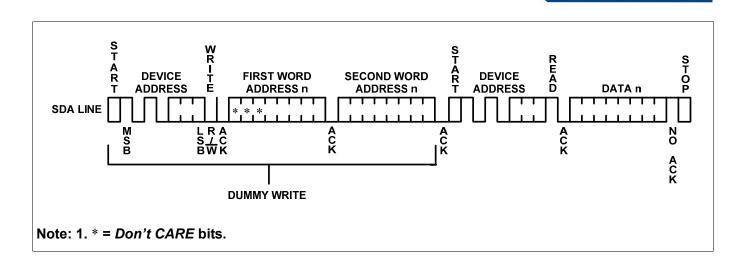


Figure 10. Random Read

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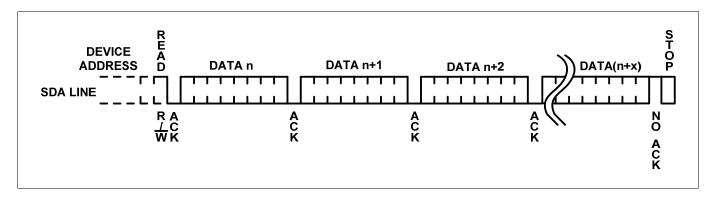
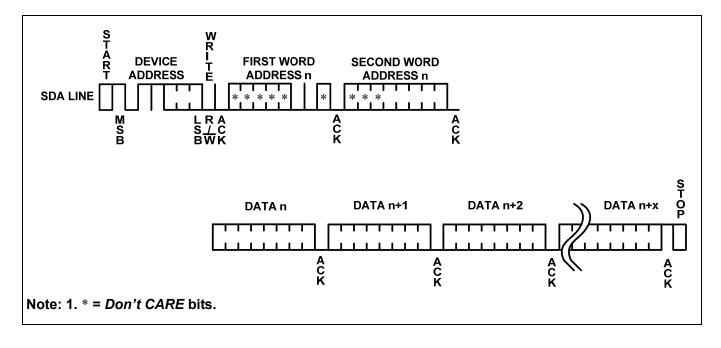


Figure 12. Write Security Sector



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Figure 13. Read Security Sector

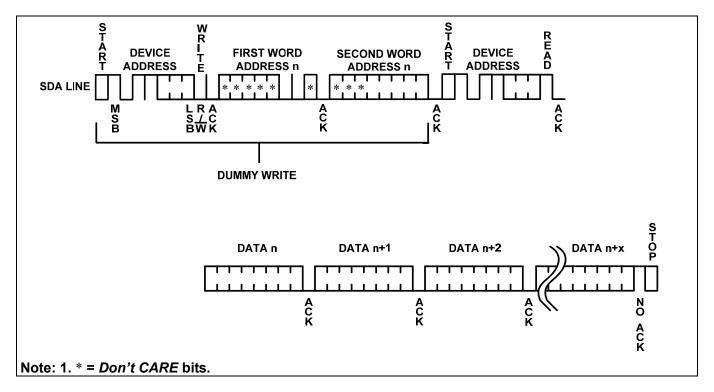


Figure 14. Lock Security Sector

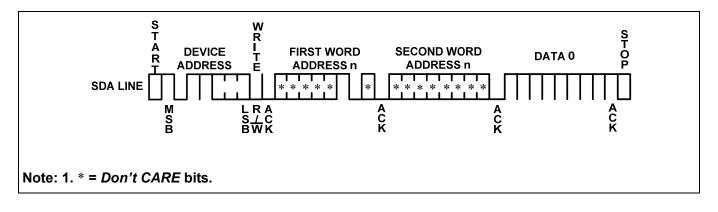


Figure 15. Read Lock Status

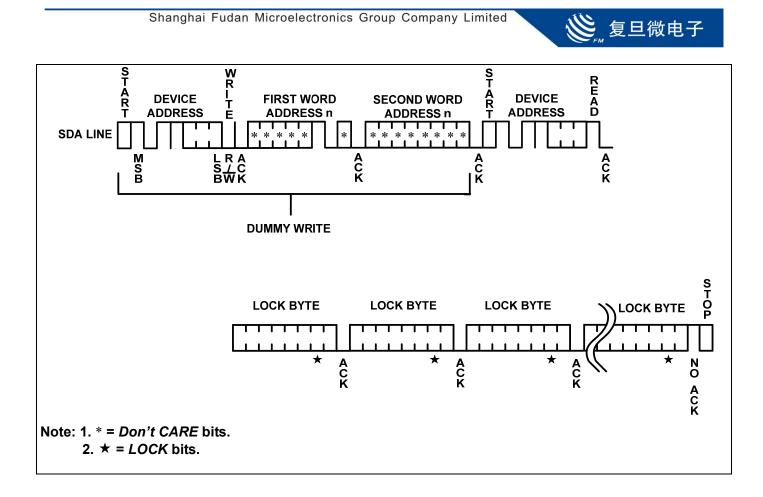
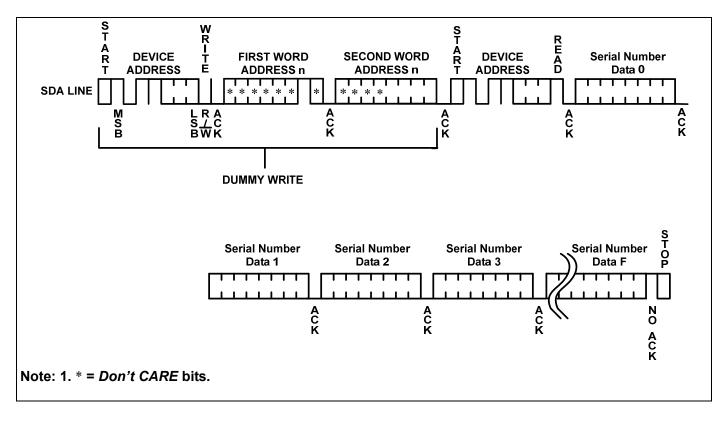


Figure 16. Read Unique ID





Ordering Information

	FM	24C	64	D -PP	-C -ŀ
Company Prefix					
FM = Shanghai Fudan Microelectronics Group Co., Itc	1				
Product Family					
24C = 2-Wire Serial EEPROM					
Product Density					
64 = 64K-bit					
Device Type					
D = with 128-bit Unique ID with 32-byte Security Sector Supply voltage from 1.7V to 5.5V Package Type ¹					
PD = 8-pin PDIP M2F or M2P = 8-pin Mod SO = 8-pin SOP TS = 8-pin TSSOP	dule P	ackage	3		
DN = 8-pin TDFN (2x3mm) ² CT = Thin 4-ball WLCSP ³					
Product Carrier					
U = Tube T = Tape and Reel R = Module Reel					
HSF ID Code ⁴					

Blank or R = RoHS Compliant G = RoHS Compliant, Halogen-free, Antimony-free

Note:

- 1. For SO, TS, DN package, MSL1 package are available, for detail please contact local sales office.
- 2. For Thinner package please contact local sales office.
- 3. For the details of WLCSP package and Module package please contact local sales office.
- 4. For PD, M2F, M2P package: R class only. For SO, TS, DN and CT package: G class only.

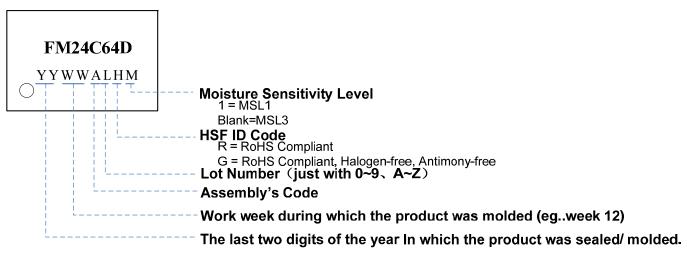


Part Marking Scheme

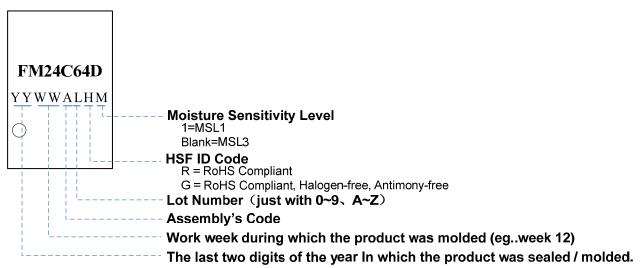
PDIP8

	FM24C64D	
P	<u>YYWWALH</u>	
		HSF ID Code
		R = RoHS Compliant
		Lot Number (just with 0~9、A~Z)
		Assembly's Code
		Work week during which the product was molded (egweek 12)
	L	The last two digits of the year In which the product was sealed/ molded.





TSSOP8



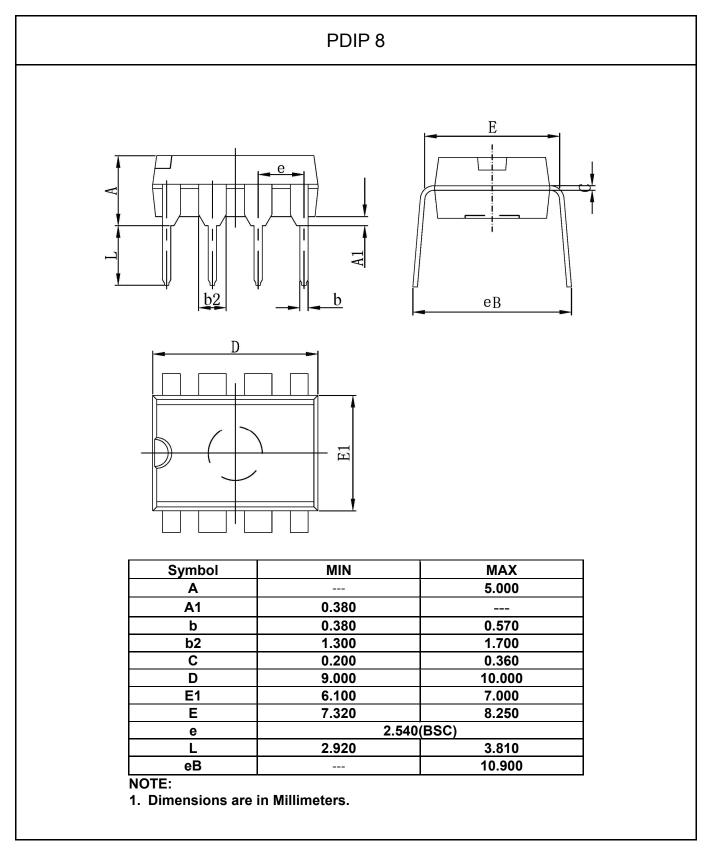


TDFN8 (2x3mm)

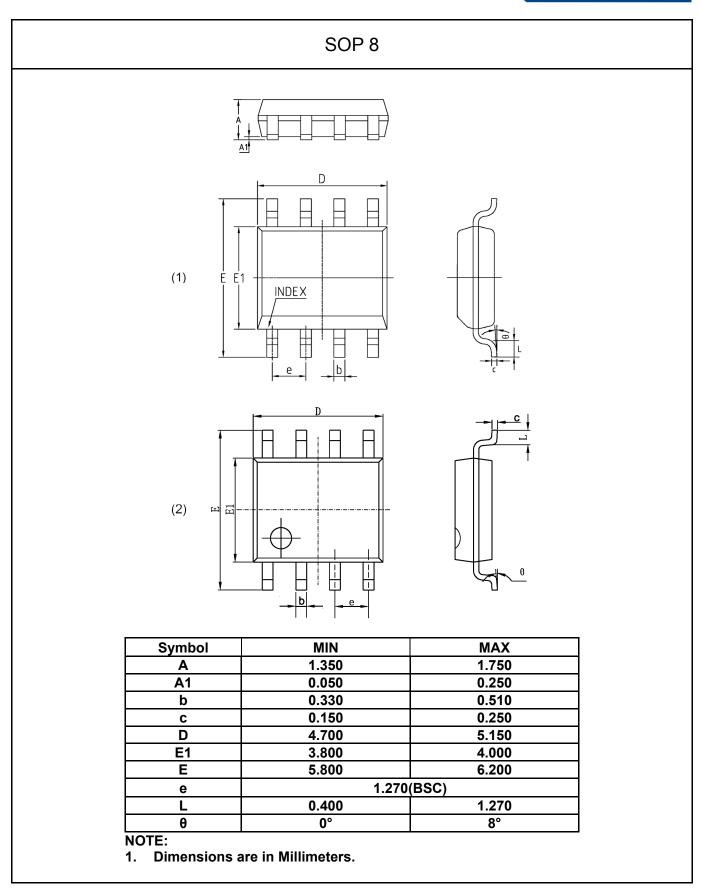
4 C 6	
	Product Density Code
· · · · · · · · · · · · · · · · · · ·	The month (hexadecimal digit) in which the product was molded.
A L H	The last one digit of year in which the product was sealed/molded
	HSF ID Code
\cup M	G = RoHS Compliant, Halogen-free, Antimony-free
	Moisture Sensitivity Level
	1=MSL1
	Lot Number(just with 0~9、A~Z)
	Assembly's Code



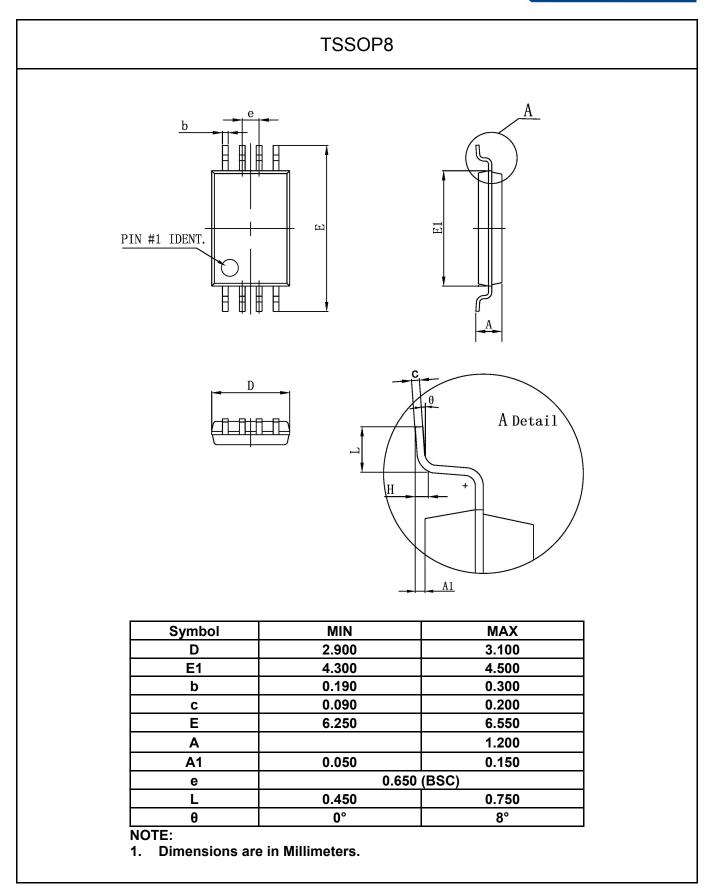
Packaging Information





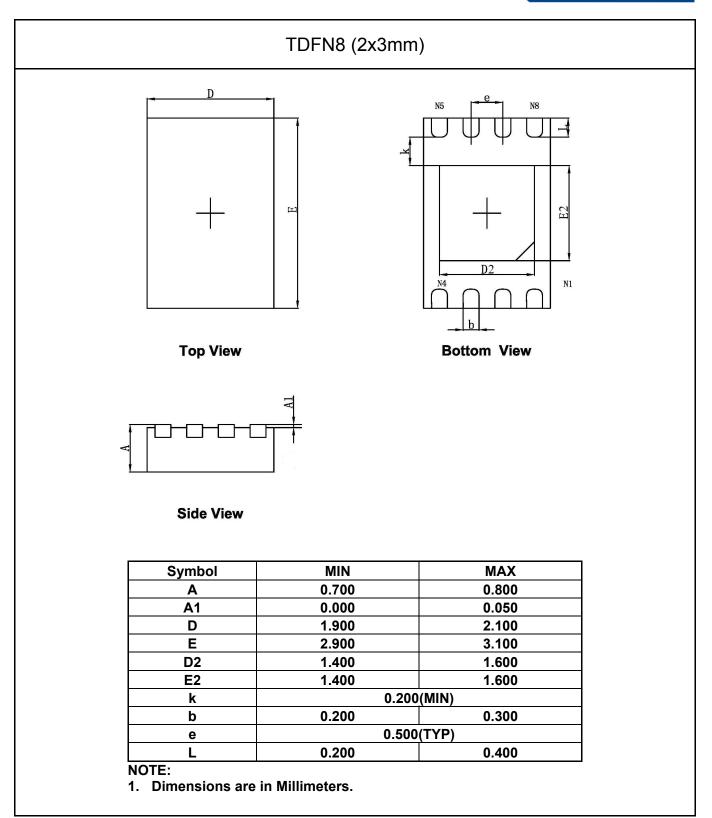














Revision History

Version	Publication date	Pages	Revise Description
1.0	Nov. 2014	28	Initial document Release.
1.1	Dec. 2014	28	Updated the chapters of packaging type, Ordering information, Part marking scheme and packaging information.
1.2	May. 2015	27	Updated the chapters of packaging type, Ordering information and packaging information.
1.3	Jun. 2015	27	 Updated the chapters of Device Addressing Corrected the typo.



Sales and Service

Shanghai Fudan Microelectronics Group Co., Ltd.

Address: Bldg No. 4, 127 Guotai Rd, Shanghai City China. Postcode: 200433 Tel: (86-021) 6565 5050 Fax: (86-021) 6565 9115

Shanghai Fudan Microelectronics (HK) Co., Ltd.

Address: Unit 506, 5/F., East Ocean Centre, 98 Granville Road, Tsimshatsui East, Kowloon, Hong Kong Tel: (852) 2116 3288 2116 3338 Fax: (852) 2116 0882

Beijing Office

Address: Room 423, Bldg B, Gehua Building, 1 QingLong Hutong, Dongzhimen Alley north Street, Dongcheng District, Beijing City, China. Postcode: 100007 Tel: (86-010) 8418 6608 Fax: (86-010) 8418 6211

Shenzhen Office

Address: Room.1301, Century Bldg, No. 4002, Shengtingyuan Hotel, Huaqiang Rd (North), Shenzhen City, China. Postcode: 518028 Tel: (86-0755) 8335 0911 8335 1011 8335 2011 8335 0611 Fax: (86-0755) 8335 9011

Shanghai Fudan Microelectronics (HK) Ltd Taiwan Representative Office

Address: Unit 1225, 12F., No 252, Sec.1 Neihu Rd., Neihu Dist., Taipei City 114, Taiwan Tel : (886-2) 7721 1890 (886-2) 7721 1889 Fax: (886-2) 7722 3888

Shanghai Fudan Microelectronics (HK) Ltd Singapore Representative Office

Address : 237, Alexandra Road, #07-01 The Alexcier, Singapore 159929 Tel : (65) 6472 3688 Fax: (65) 6472 3669

Shanghai Fudan Microelectronics Group Co., Ltd NA Office

Address :2490 W. Ray Road Suite#2 Chandler, AZ 85224 USA Tel : (480) 857-6500 ext 18

Web Site: http://www.fmsh.com/

上海复旦微电子集团股份有限公司